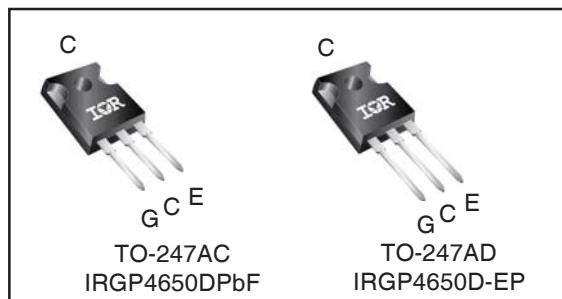
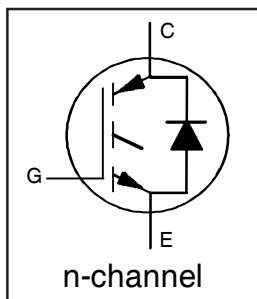


INSULATED GATE BIPOLAR TRANSISTOR WITH ULTRAFAST SOFT RECOVERY DIODE

$V_{CES} = 600V$
$I_C = 50A, T_C = 100^\circ C$
$t_{SC} \geq 5\mu s, T_{J(max)} = 175^\circ C$
$V_{CE(on)} \text{ typ.} = 1.60V @ I_C = 35A$



G	C	E
Gate	Collector	Emitter

Applications

- Industrial Motor Drive
- Inverters
- UPS
- Welding

Features	Benefits
Low $V_{CE(ON)}$ and Switching Losses	High efficiency in a wide range of applications and switching frequencies
Square RBSOA and Maximum Junction Temperature 175°C	Improved reliability due to rugged hard switching performance and higher power capability
Positive $V_{CE(ON)}$ Temperature Coefficient	Excellent current sharing in parallel operation
5 μs short circuit SOA	Enables short circuit protection scheme
Lead-Free, RoHS compliant	Environmentally friendly

Base part number	Package Type	Standard Pack		Orderable part number
		Form	Quantity	
IRGP4650DPbF	TO-247AC	Tube	25	IRGP4650DPbF
IRGP4650D-EPbF	TO-247AD	Tube	25	IRGP4650D-EPbF

Absolute Maximum Ratings

	Parameter	Max.	Units
V_{CES}	Collector-to-Emitter Voltage	600	V
$I_C @ T_C = 25^\circ C$	Continuous Collector Current	76	A
$I_C @ T_C = 100^\circ C$	Continuous Collector Current	50	
I_{CM}	Pulse Collector Current, $V_{GE} = 15V$	105	
I_{LM}	Clamped Inductive Load Current, $V_{GE} = 20V$ ①	140	
$I_F @ T_C = 25^\circ C$	Diode Continuous Forward Current	76	
$I_F @ T_C = 100^\circ C$	Diode Continuous Forward Current	50	V
I_{FM}	Diode Maximum Forward Current ④	140	
V_{GE}	Continuous Gate-to-Emitter Voltage	± 20	
	Transient Gate-to-Emitter Voltage	± 30	
$P_D @ T_C = 25^\circ C$	Maximum Power Dissipation	268	W
$P_D @ T_C = 100^\circ C$	Maximum Power Dissipation	134	
T_J	Operating Junction and	-55 to +175	°C
T_{STG}	Storage Temperature Range		
	Soldering Temperature, for 10 sec.	300 (0.063 in. (1.6mm) from case)	
	Mounting Torque, 6-32 or M3 Screw	10 lbf-in (1.1 N-m)	

Thermal Resistance

	Parameter	Min.	Typ.	Max.	Units
$R_{\theta JC}$ (IGBT)	Junction-to-Case (IGBT) ②	—	—	0.56	°C/W
$R_{\theta JC}$ (Diode)	Junction-to-Case (Diode) ②	—	—	1.0	
$R_{\theta CS}$	Case-to-Sink (flat, greased surface)	—	0.24	—	
$R_{\theta JA}$	Junction-to-Ambient (typical socket mount)	—	—	40	

Electrical Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
V _{(BR)CES}	Collector-to-Emitter Breakdown Voltage	600	—	—	V	V _{GE} = 0V, I _C = 100μA ③
ΔV _{(BR)CES} /ΔT _J	Temperature Coeff. of Breakdown Voltage	—	1.3	—	mV/°C	V _{GE} = 0V, I _C = 1mA (25°C-175°C)
V _{CE(on)}	Collector-to-Emitter Saturation Voltage	—	1.60	1.90	V	I _C = 35A, V _{GE} = 15V, T _J = 25°C
		—	1.90	—		I _C = 35A, V _{GE} = 15V, T _J = 150°C
		—	2.00	—		I _C = 35A, V _{GE} = 15V, T _J = 175°C
V _{GE(th)}	Gate Threshold Voltage	4.0	—	6.5	V	V _{CE} = V _{GE} , I _C = 1.0mA
ΔV _{GE(th)} /ΔT _J	Threshold Voltage temp. coefficient	—	-18	—	mV/°C	V _{CE} = V _{GE} , I _C = 1.0mA (25°C - 175°C)
g _f e	Forward Transconductance	—	25	—	S	V _{CE} = 50V, I _C = 35A, PW = 60μs
I _{CES}	Collector-to-Emitter Leakage Current	—	1.0	70	μA	V _{GE} = 0V, V _{CE} = 600V
		—	770	—		V _{GE} = 0V, V _{CE} = 600V, T _J = 175°C
V _{FM}	Diode Forward Voltage Drop	—	2.0	3.0	V	I _F = 35A
		—	1.4	—		I _F = 35A, T _J = 175°C
I _{GES}	Gate-to-Emitter Leakage Current	—	—	±100	nA	V _{GE} = ±20V

Switching Characteristics @ T_J = 25°C (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
Q _g	Total Gate Charge (turn-on)	—	69	104	nC	I _C = 35A V _{GE} = 15V V _{CC} = 400V
Q _{ge}	Gate-to-Emitter Charge (turn-on)	—	18	27		
Q _{gc}	Gate-to-Collector Charge (turn-on)	—	29	44		
E _{on}	Turn-On Switching Loss	—	390	508	μJ	I _C = 35A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 200μH, L _S = 150nH, T _J = 25°C Energy losses include tail & diode reverse recovery ⑤
E _{off}	Turn-Off Switching Loss	—	632	753		
E _{total}	Total Switching Loss	—	1022	1261		
t _{d(on)}	Turn-On delay time	—	46	56	ns	I _C = 35A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 200μH, L _S = 150nH, T _J = 25°C
t _r	Rise time	—	33	42		
t _{d(off)}	Turn-Off delay time	—	105	117		
t _f	Fall time	—	44	54		
E _{on}	Turn-On Switching Loss	—	1013	—		
E _{off}	Turn-Off Switching Loss	—	929	—	μJ	I _C = 35A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 200μH, L _S = 150nH, T _J = 175°C Energy losses include tail & diode reverse recovery ⑤
E _{total}	Total Switching Loss	—	1942	—		
t _{d(on)}	Turn-On delay time	—	43	—		
t _r	Rise time	—	35	—	ns	I _C = 35A, V _{CC} = 400V, V _{GE} = 15V R _G = 10Ω, L = 200μH, L _S = 150nH T _J = 175°C
t _{d(off)}	Turn-Off delay time	—	127	—		
t _f	Fall time	—	61	—		
C _{ies}	Input Capacitance	—	2113	—	pF	V _{GE} = 0V V _{CC} = 30V f = 1.0Mhz
C _{oes}	Output Capacitance	—	197	—		
C _{res}	Reverse Transfer Capacitance	—	65	—		
RBSOA	Reverse Bias Safe Operating Area	FULL SQUARE				T _J = 175°C, I _C = 140A V _{CC} = 480V, V _p ≤ 600V R _G = 10Ω, V _{GE} = +20V to 0V
SCSOA	Short Circuit Safe Operating Area	5	—	—	μs	V _{CC} = 400V, V _p ≤ 600V R _G = 10Ω, V _{GE} = +15V to 0V
E _{rec}	Reverse Recovery Energy of the Diode	—	304	—	μJ	T _J = 175°C
t _{rr}	Diode Reverse Recovery Time	—	120	—	ns	V _{CC} = 400V, I _F = 35A
I _{rr}	Peak Reverse Recovery Current	—	25	—	A	V _{GE} = 15V, R _G = 10Ω, L = 210μH, L _S = 150nH

Notes:

- ① V_{CC} = 80% (V_{CES}), V_{GE} = 20V, L = 19μH, R_G = 10Ω.
- ② R_θ is measured at T_J of approximately 90°C.
- ③ Refer to AN-1086 for guidelines for measuring V_{(BR)CES} safely.
- ④ Pulse width limited by max. junction temperature.
- ⑤ Values influenced by parasitic L and C in measurement.

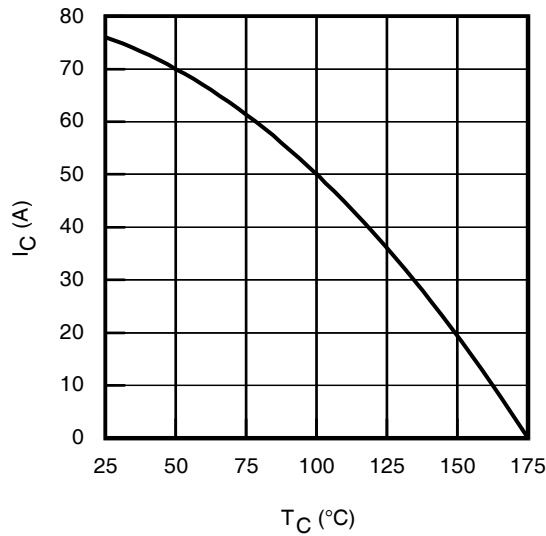


Fig. 1 - Maximum DC Collector Current vs. Case Temperature

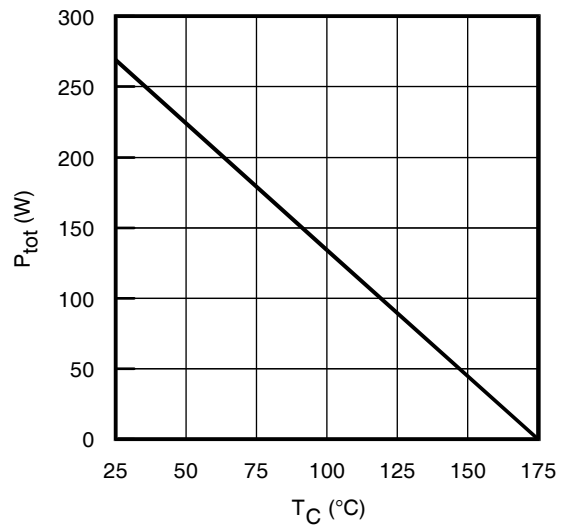


Fig. 2 - Power Dissipation vs. Case Temperature

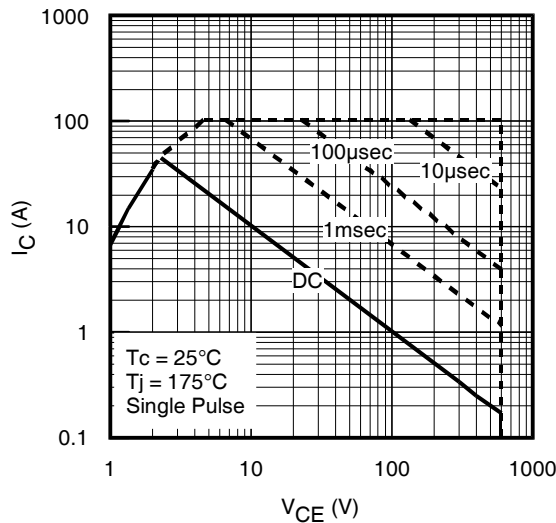


Fig. 3 - Forward SOA
 $T_C = 25^\circ\text{C}$, $T_J \leq 175^\circ\text{C}$; $V_{GE} = 15\text{V}$

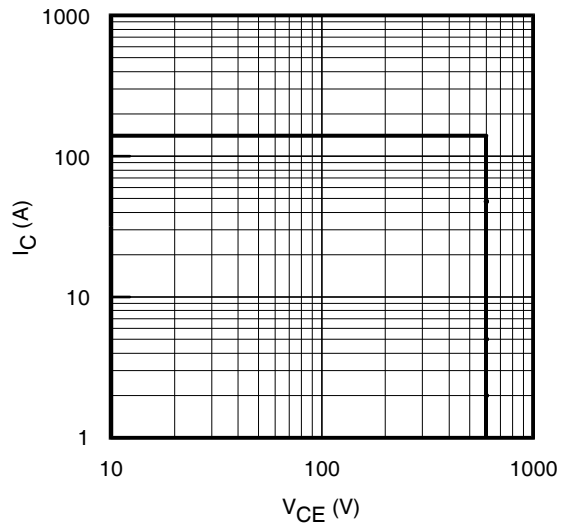


Fig. 4 - Reverse Bias SOA
 $T_J = 175^\circ\text{C}$; $V_{GE} = 20\text{V}$

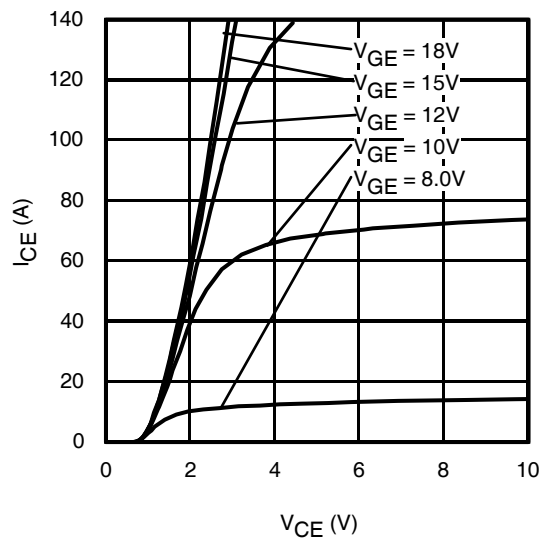


Fig. 5 - Typ. IGBT Output Characteristics
 $T_J = -40^\circ\text{C}$; $t_p \leq 60\mu\text{s}$

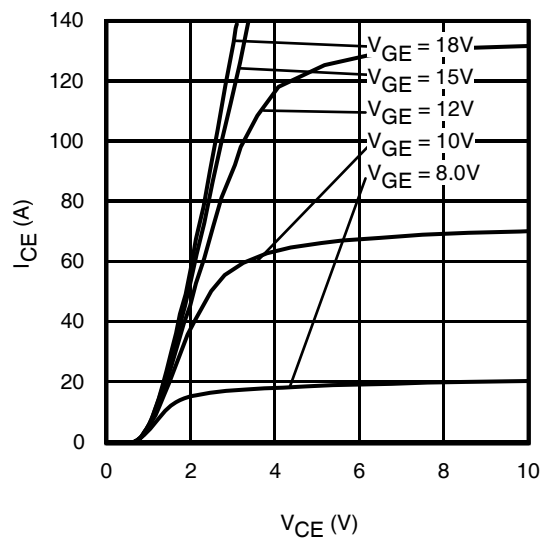


Fig. 6 - Typ. IGBT Output Characteristics
 $T_J = 25^\circ\text{C}$; $t_p \leq 60\mu\text{s}$

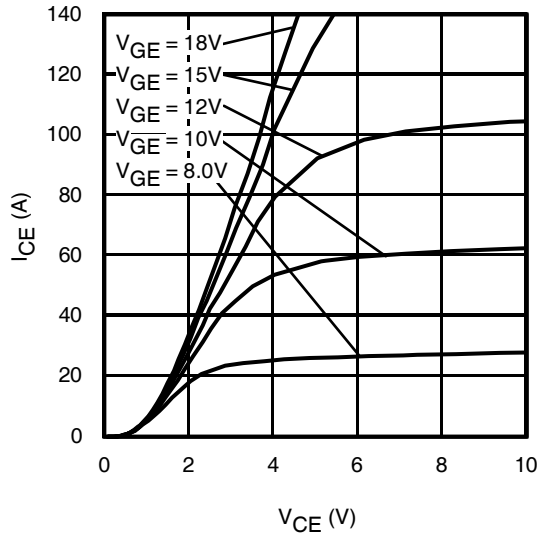


Fig. 7 - Typ. IGBT Output Characteristics
 $T_J = 175^\circ\text{C}$; $t_p = \leq 60\mu\text{s}$

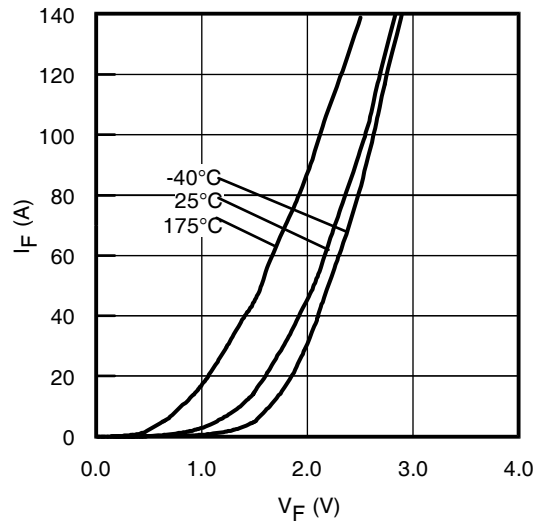


Fig. 8 - Typ. Diode Forward Characteristics
 $t_p = 80\mu\text{s}$

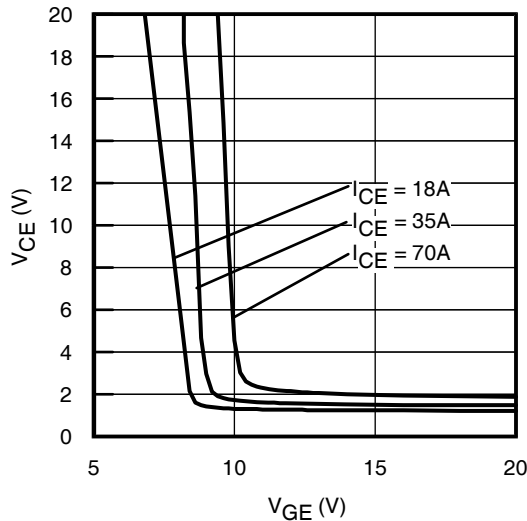


Fig. 9 - Typical V_{CE} vs. V_{GE}
 $T_J = -40^\circ\text{C}$

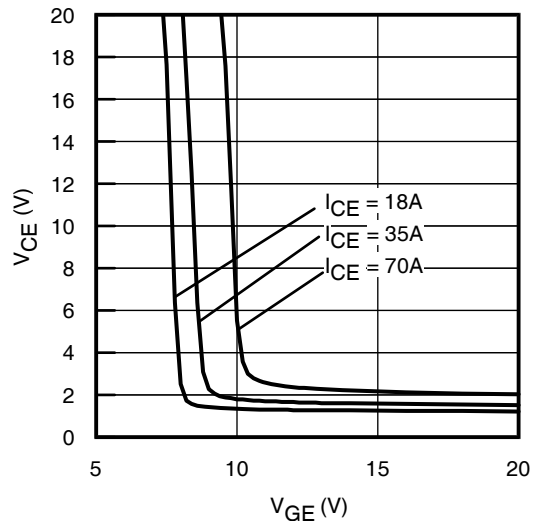


Fig. 10 - Typical V_{CE} vs. V_{GE}
 $T_J = 25^\circ\text{C}$

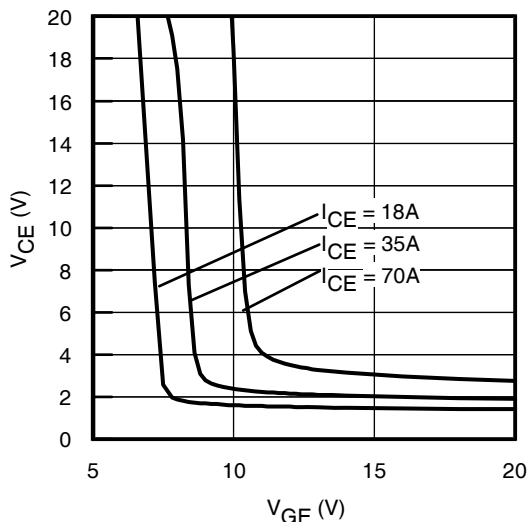


Fig. 11 - Typical V_{CE} vs. V_{GE}
 $T_J = 175^\circ\text{C}$

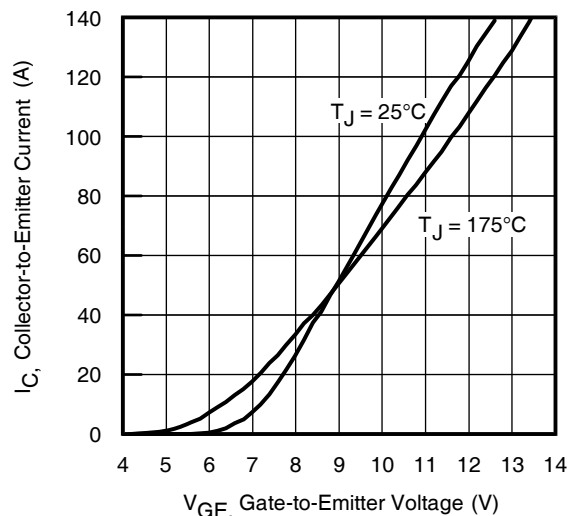
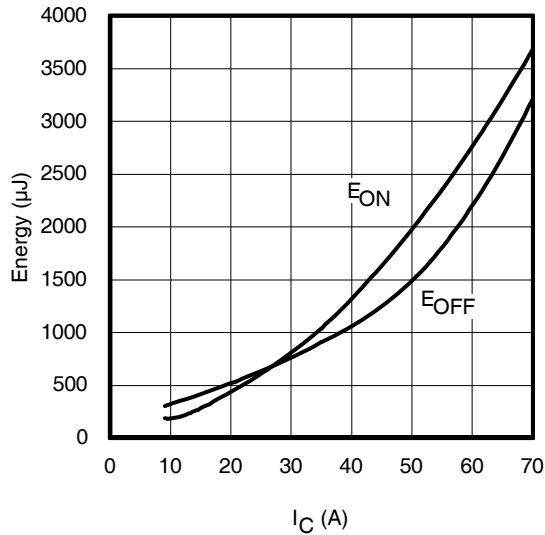
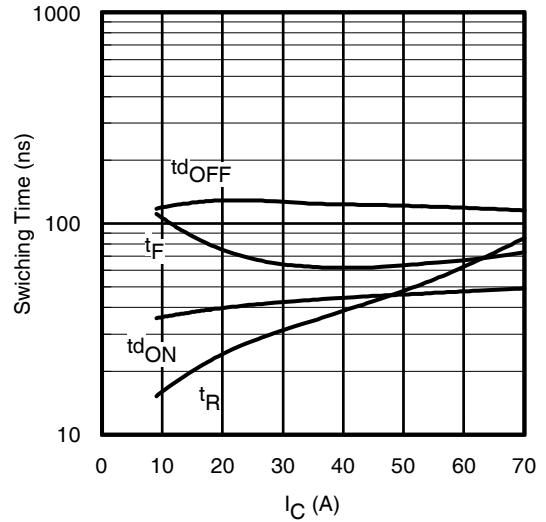
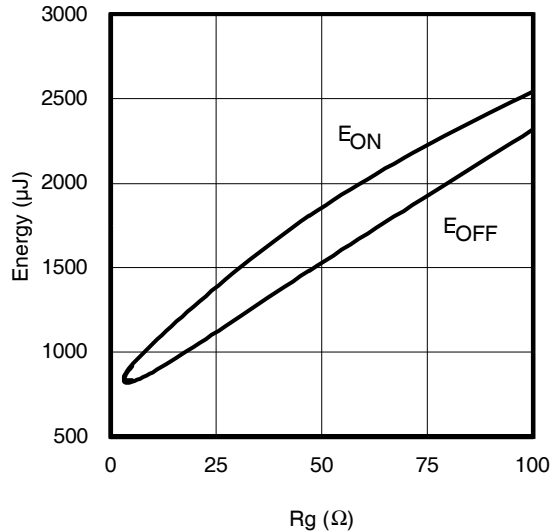
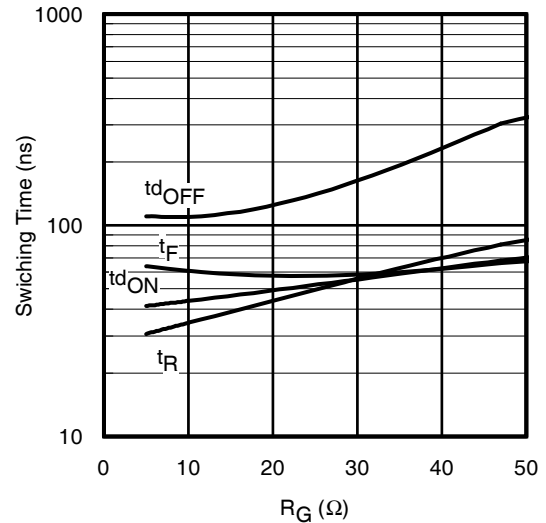
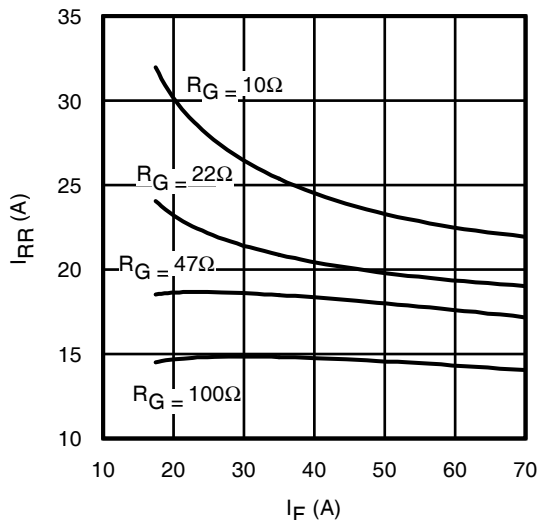
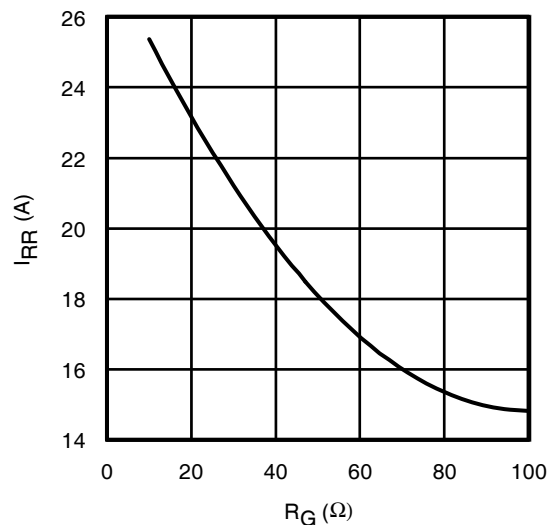


Fig. 12 - Typ. Transfer Characteristics
 $V_{CE} = 50\text{V}$; $t_p = 60\mu\text{s}$


Fig. 13 - Typ. Energy Loss vs. I_C
 $T_J = 175^\circ\text{C}; L = 200\mu\text{H}; V_{CE} = 400\text{V}, R_G = 10\Omega; V_{GE} = 15\text{V}$

Fig. 14 - Typ. Switching Time vs. I_C
 $T_J = 175^\circ\text{C}; L = 200\mu\text{H}; V_{CE} = 400\text{V}, R_G = 10\Omega; V_{GE} = 15\text{V}$

Fig. 15 - Typ. Energy Loss vs. R_G
 $T_J = 175^\circ\text{C}; L = 210\mu\text{H}; V_{CE} = 400\text{V}, I_{CE} = 35\text{A}; V_{GE} = 15\text{V}$

Fig. 16 - Typ. Switching Time vs. R_G
 $T_J = 175^\circ\text{C}; L = 210\mu\text{H}; V_{CE} = 400\text{V}, I_{CE} = 35\text{A}; V_{GE} = 15\text{V}$

Fig. 17 - Typ. Diode I_{RR} vs. I_F
 $T_J = 175^\circ\text{C}$

Fig. 18 - Typ. Diode I_{RR} vs. R_G
 $T_J = 175^\circ\text{C}$

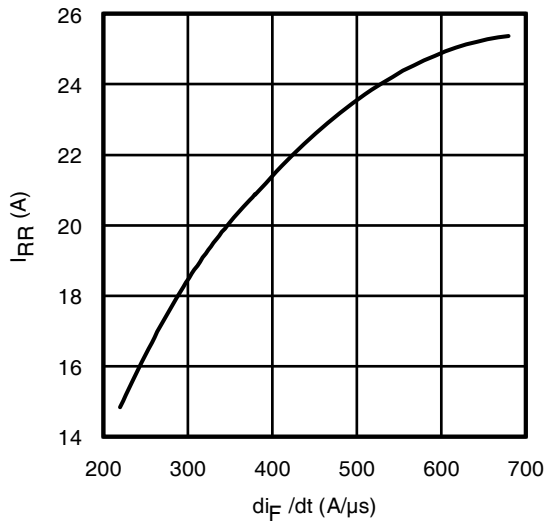


Fig. 19 - Typ. Diode I_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $I_F = 35A$; $T_J = 175^\circ C$

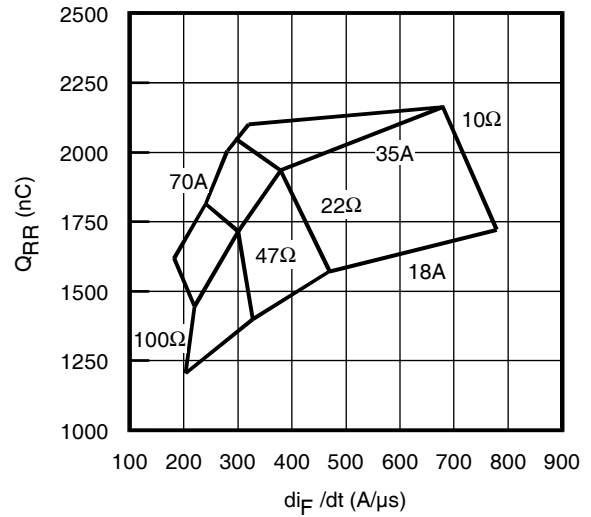


Fig. 20 - Typ. Diode Q_{RR} vs. di_F/dt
 $V_{CC} = 400V$; $V_{GE} = 15V$; $T_J = 175^\circ C$

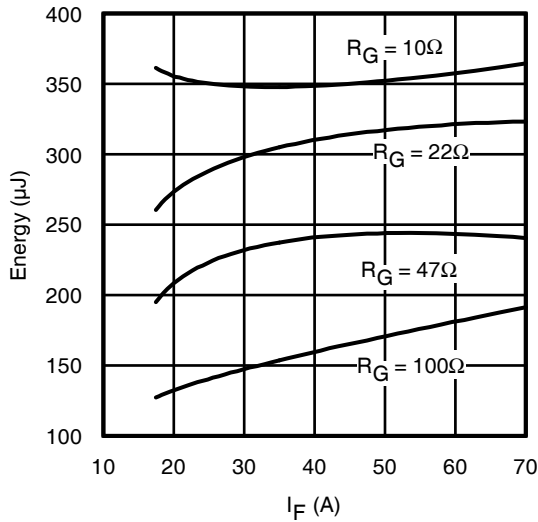


Fig. 21 - Typ. Diode E_{RR} vs. I_F
 $T_J = 175^\circ C$

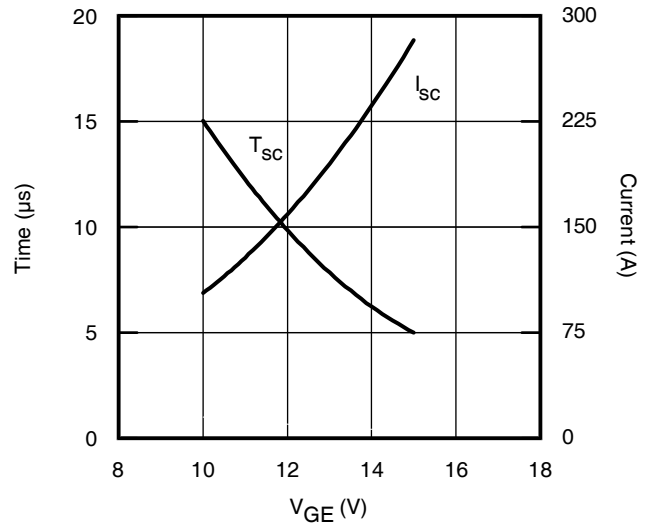


Fig. 22 - V_{GE} vs. Short Circuit Time
 $V_{CC} = 400V$; $T_C = 25^\circ C$

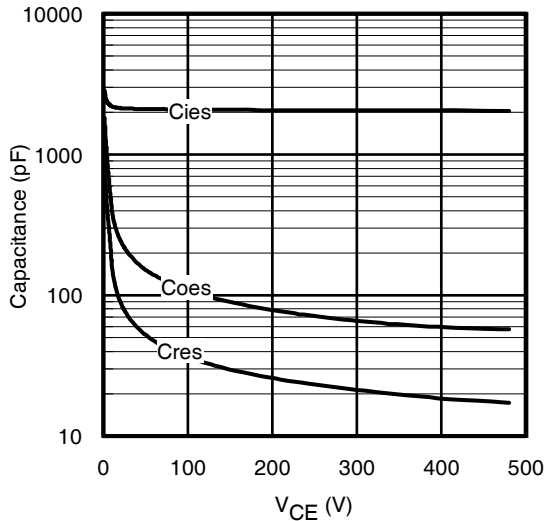


Fig. 23 - Typ. Capacitance vs. V_{CE}
 $V_{GE} = 0V$; $f = 1MHz$

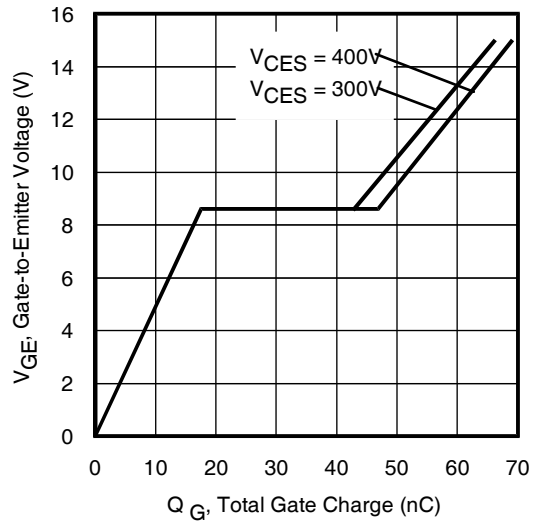


Fig. 24 - Typical Gate Charge vs. V_{GE}
 $I_{CE} = 35A$; $L = 740\mu H$

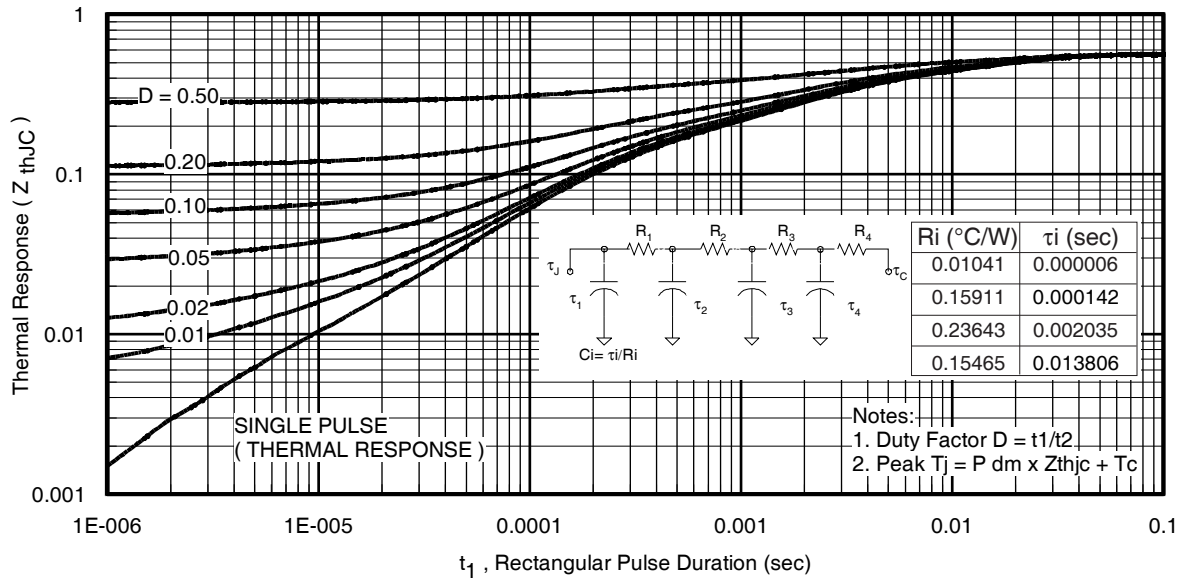


Fig 25. Maximum Transient Thermal Impedance, Junction-to-Case (IGBT)

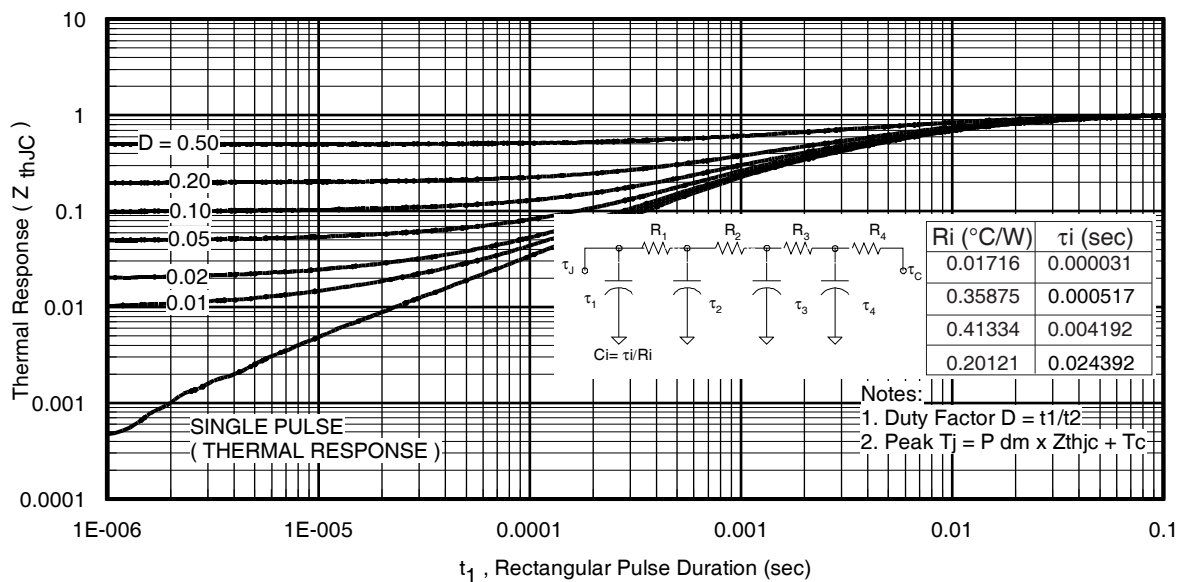
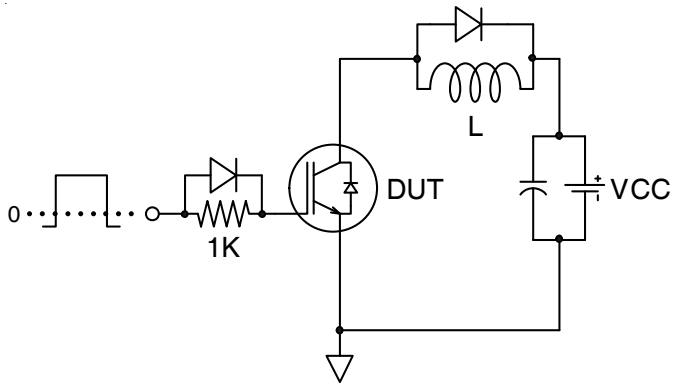
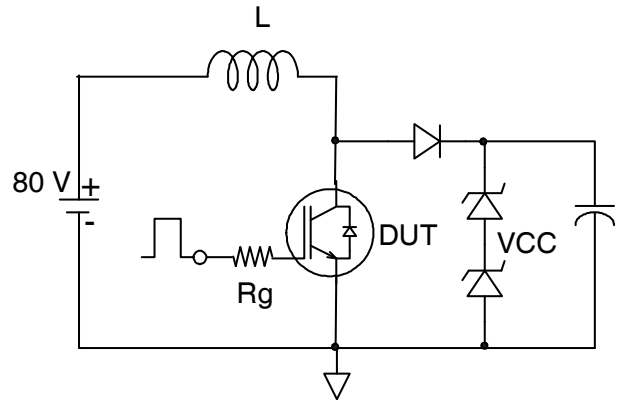
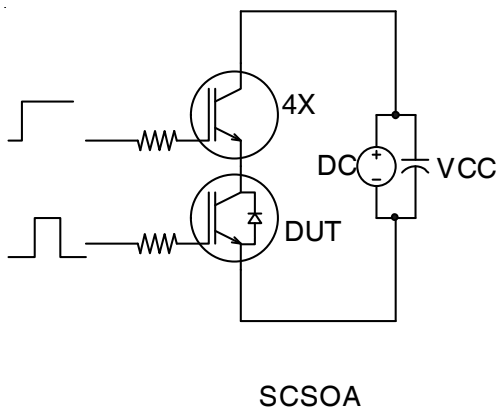
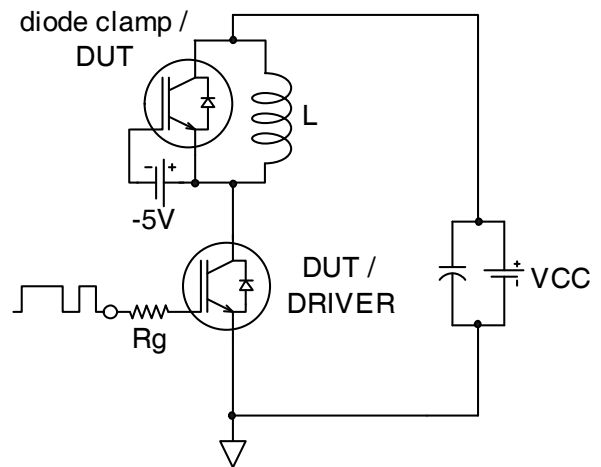
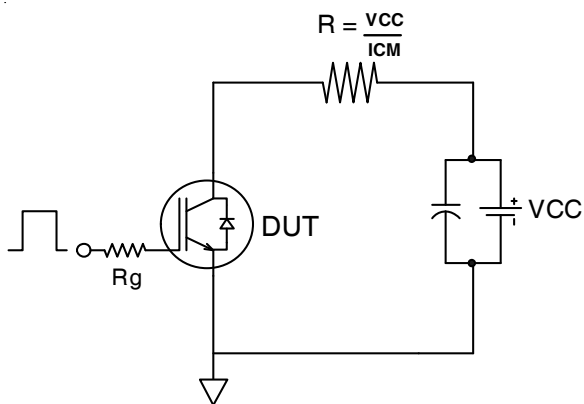
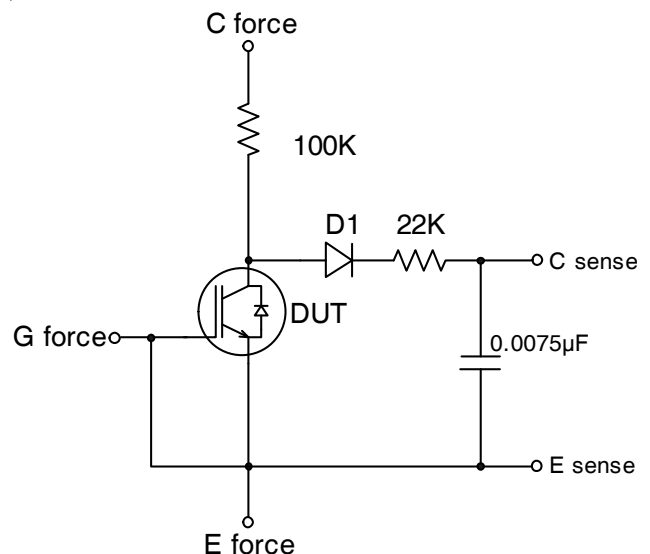


Fig. 26. Maximum Transient Thermal Impedance, Junction-to-Case (DIODE)


Fig.C.T.1 - Gate Charge Circuit (turn-off)

Fig.C.T.2 - RBSOA Circuit

Fig.C.T.3 - S.C. SOA Circuit

Fig.C.T.4 - Switching Loss Circuit

Fig.C.T.5 - Resistive Load Circuit

Fig.C.T.6 - BVCES Filter Circuit

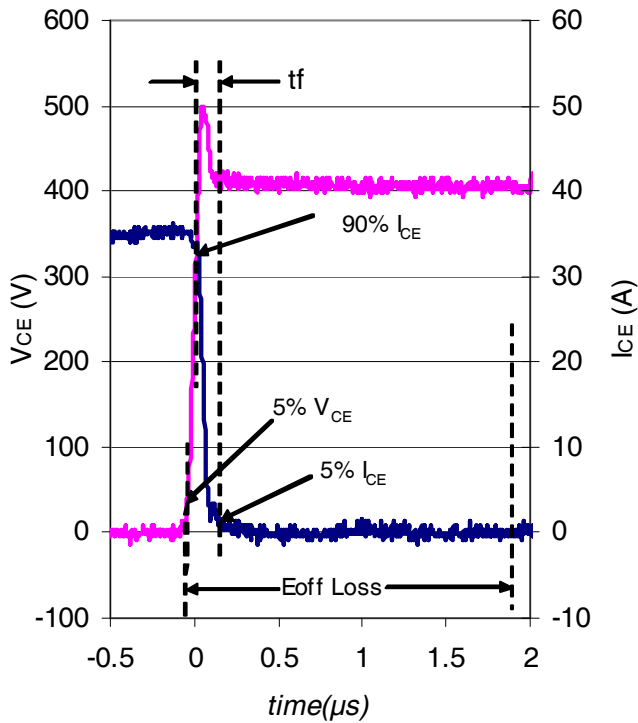


Fig. WF1 - Typ. Turn-off Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

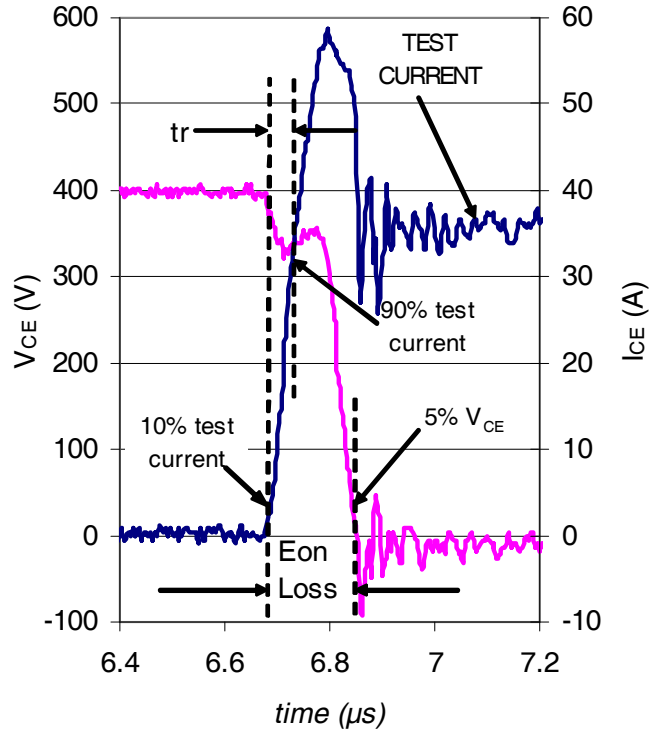


Fig. WF2 - Typ. Turn-on Loss Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

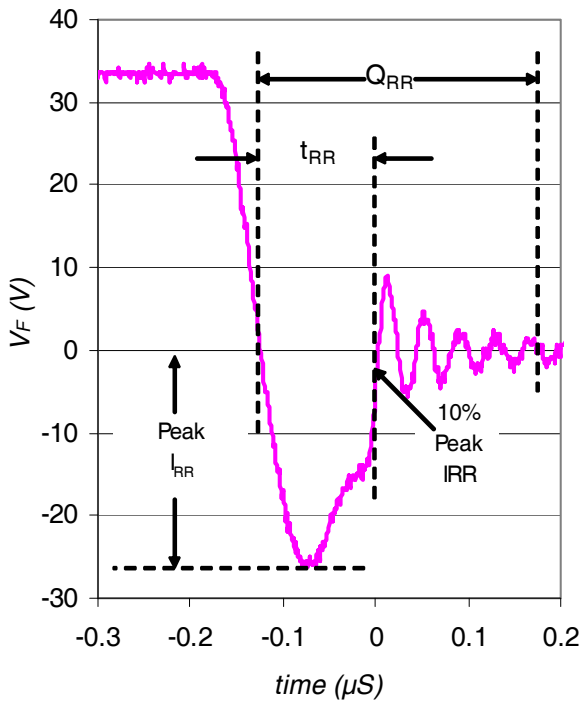


Fig. WF3 - Typ. Diode Recovery Waveform
@ $T_J = 175^\circ\text{C}$ using Fig. CT.4

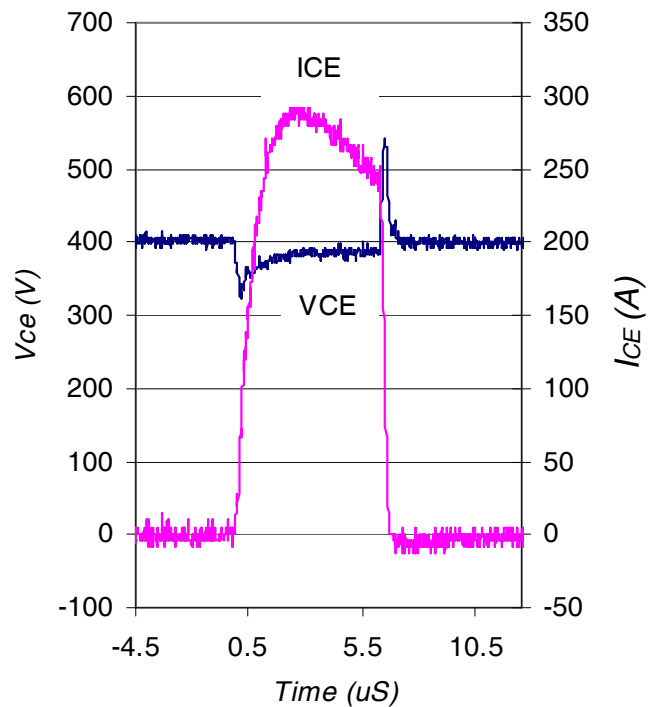
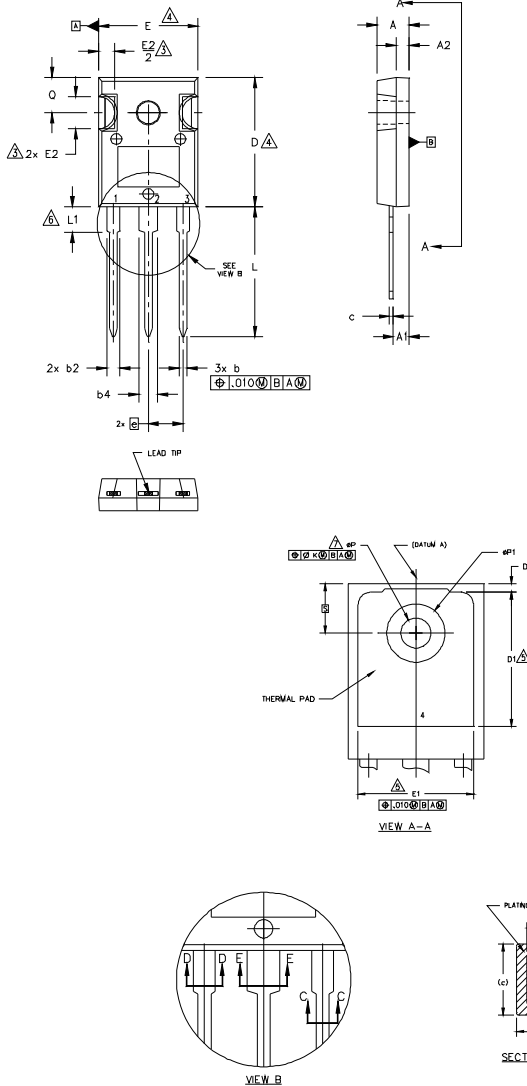


Fig. WF4 - Typ. S.C. Waveform
@ $T_J = 25^\circ\text{C}$ using Fig. CT.3

TO-247AD Package Outline

Dimensions are shown in millimeters (inches)



NOTES:

1. DIMENSIONING AND TOLERANCING AS PER ASME Y14.5M 1994.
2. DIMENSIONS ARE SHOWN IN INCHES.
3. CONTOUR OF SLOT OPTIONAL.
4. DIMENSION D & E DO NOT INCLUDE MOLD FLASH. MOLD FLASH SHALL NOT EXCEED .005" (0.127) PER SIDE. THESE DIMENSIONS ARE MEASURED AT THE OUTERMOST EXTREMES OF THE PLASTIC BODY.
5. THERMAL PAD CONTOUR OPTIONAL WITHIN DIMENSIONS D1 & E1.
6. LEAD FINISH UNCONTROLLED IN L1.
7. ØP TO HAVE A MAXIMUM DRAFT ANGLE OF 1.5 ° TO THE TOP OF THE PART WITH A MAXIMUM HOLE DIAMETER OF .154 INCH.
8. OUTLINE CONFORMS TO JEDEC OUTLINE TO-247AD.

SYMBOL	DIMENSIONS				NOTES
	INCHES		MILLIMETERS		
	MIN.	MAX.	MIN.	MAX.	
A	.183	.209	4.65	5.31	
A1	.087	.102	2.21	2.59	
A2	.059	.098	1.50	2.49	
b	.039	.055	0.99	1.40	
b1	.039	.053	0.99	1.35	
b2	.065	.094	1.65	2.39	
b3	.065	.092	1.65	2.34	
b4	.102	.135	2.59	3.43	
b5	.102	.133	2.59	3.38	
c	.015	.035	0.38	0.89	
c1	.015	.033	0.38	0.84	
D	.776	.815	19.71	20.70	4
D1	.515	-	13.08	-	5
D2	.020	.053	0.51	1.35	
E	.602	.625	15.29	15.87	4
E1	.530	-	13.46	-	
E2	.178	.216	4.52	5.49	
e	.215 BSC		5.46 BSC		
Øk	.010		0.25		
L	.780	.827	19.57	21.00	
L1	.146	.169	3.71	4.29	
ØP	.140	.144	3.56	3.66	
ØP1	-	.291	-	7.39	
Q	.209	.224	5.31	5.69	
S	.217 BSC		5.51 BSC		

LEAD ASSIGNMENTS

HEXFET

- 1.- GATE
- 2.- DRAIN
- 3.- SOURCE
- 4.- DRAIN

IGBTs, CoPACK

- 1.- GATE
- 2.- COLLECTOR
- 3.- EMITTER
- 4.- COLLECTOR

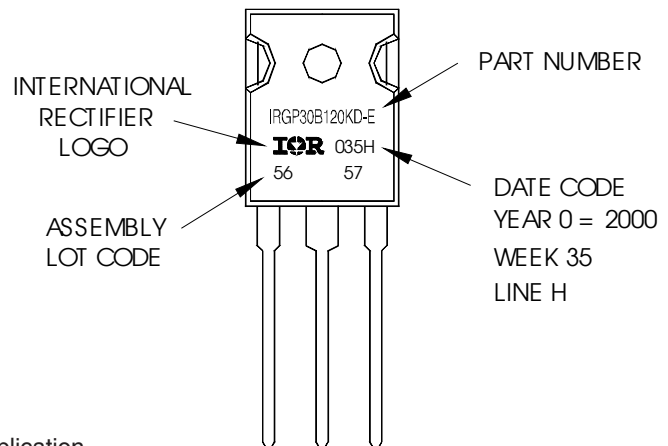
DIODES

- 1.- ANODE/OPEN
- 2.- CATHODE
- 3.- ANODE

TO-247AD Part Marking Information

EXAMPLE: THIS IS AN IRGP30B120KD-E
WITH ASSEMBLY
LOT CODE 5657
ASSEMBLED ON WW 35, 2000
IN THE ASSEMBLY LINE "H"

Note: "P" in assembly line position
indicates "Lead-Free"



TO-247AD package is not recommended for Surface Mount Application.

Note: For the most current drawing please refer to IR website at <http://www.irf.com/package/>

Qualification Information[†]

Qualification Level	Industrial (per International Rectifier's internal guidelines)	
Moisture Sensitivity Level	TO-247AC	N/A
	TO-247AD	N/A
RoHS Compliant	Yes	

† Qualification standards can be found at International Rectifier's web site: <http://www.irf.com/product-info/reliability>

†† Highest passing voltage.

Revision History

Date	Comments
11/17/2014	<ul style="list-style-type: none"> • Added note ④ to I_{FM} Diode Maximum Forward Current on page 1. • Added note ⑤ to switching losses test condition on page 2.

Данный компонент на территории Российской Федерации

Вы можете приобрести в компании MosChip.

Для оперативного оформления запроса Вам необходимо перейти по данной ссылке:

<http://moschip.ru/get-element>

Вы можете разместить у нас заказ для любого Вашего проекта, будь то серийное производство или разработка единичного прибора.

В нашем ассортименте представлены ведущие мировые производители активных и пассивных электронных компонентов.

Нашей специализацией является поставка электронной компонентной базы двойного назначения, продукции таких производителей как XILINX, Intel (ex.ALTERA), Vicor, Microchip, Texas Instruments, Analog Devices, Mini-Circuits, Amphenol, Glenair.

Сотрудничество с глобальными дистрибьюторами электронных компонентов, предоставляет возможность заказывать и получать с международных складов практически любой перечень компонентов в оптимальные для Вас сроки.

На всех этапах разработки и производства наши партнеры могут получить квалифицированную поддержку опытных инженеров.

Система менеджмента качества компании отвечает требованиям в соответствии с ГОСТ Р ИСО 9001, ГОСТ РВ 0015-002 и ЭС РД 009

Офис по работе с юридическими лицами:

105318, г.Москва, ул.Щербаковская д.3, офис 1107, 1118, ДЦ «Щербаковский»

Телефон: +7 495 668-12-70 (многоканальный)

Факс: +7 495 668-12-70 (доб.304)

E-mail: info@moschip.ru

Skype отдела продаж:

moschip.ru

moschip.ru_4

moschip.ru_6

moschip.ru_9